

In the Claims:

1. (Currently Amended) A method of protecting devices formed in a substrate from shining spots present in a periphery of said substrate, said method comprising:

forming a ring of organic material atop said substrate to separate said periphery of said substrate from a further region of said substrate wherein said devices are formed.

2. (Original) The method of claim 1 wherein said forming step comprises forming said ring of material atop a hard mask layer that is disposed atop said substrate.

3. (Original) The method of claim 1 wherein said forming step comprises depositing material in a region between said periphery of said substrate and said further region of said substrate.

4. (Original) The method of claim 1 wherein said forming step comprises depositing material atop all of said substrate and then patterning said material to form said ring of material.

5. (Original) The method of claim 1 wherein said ring of material includes at least one of a resist layer and another organic material.

6. (Original) The method of claim 1 wherein said substrate is silicon.

7. (Currently Amended) A method of forming at least one device in a substrate, said method comprising:

depositing a layer of resist atop said substrate, wherein said layer of resist comprises a positive resist;

patterning said layer of resist to form a ring of resist atop said substrate, said ring of resist separating a periphery of said substrate from a further region of said substrate, wherein said layer of resist is patterned by exposing said layer of resist except for said ring of resist and then removing an exposed portion of said resist;

depositing a further layer of resist atop said substrate and atop said ring of resist; and patterning said further layer of resist to form at least one patterned region within said further region of said substrate.

8. (Original) The method of claim 7 further comprising:

depositing a pad oxide layer atop said substrate, depositing a pad nitride layer atop said pad oxide layer, and depositing a hard mask layer atop said nitride layer;

and wherein said forming step comprises forming said ring of material atop said hard mask layer.

9. (Withdrawn) The method of claim 8 further comprising:

etching said hard mask layer using said patterned further layer of resist and said ring of resist as an etch mask;

and etching at least one trench region in said substrate using said hard mask layer and said ring of resist as an etch mask.

10. (Withdrawn) The method of claim 9 wherein said ring of resist is of sufficient thickness that a region of said hard mask layer that is beneath said ring of resist remains after said trench region is etched.

11. (Original) The method of claim 7 wherein said ring of resist is of sufficient thickness that a region of said further layer of resist that is atop said ring of resist is not patterned during said step of patterning said further layer of resist.

12-13. (Canceled)

14. (Original) The method of claim 7 wherein said substrate is silicon.

15-25. (Canceled)

26. (Currently Amended) A method of forming a semiconductor device, the method comprising:

providing a substrate that includes a periphery region that surrounds a device, wherein a plurality of devices are to be formed in the device region; and

forming a ring of material over the substrate to separate the periphery region from the device region, wherein the ring of material is deposited onto the periphery region without a lithographic step.

27. (Previously Presented) The method of claim 26 wherein said forming step comprises forming said ring of material over a hard mask layer that is disposed over said substrate.

28. (Previously Presented) The method of claim 26 wherein said forming step comprises depositing material in a region between said periphery region and said device region.

29. (Canceled)

30. (Previously Presented) The method of claim 26 wherein said ring of material comprises a resist layer.

31. (Previously Presented) The method of claim 26 wherein said ring of material comprises an organic material.

32. (Previously Presented) The method of claim 26 wherein said substrate is silicon.

33. (Currently Amended) The method of claim 26 and further comprising:
depositing a layer of resist over the substrate, including over the periphery region and in the ring of material patterning the layer of resist; and
~~effecting~~ altering the substrate in alignment with the patterned layer of resist.

34. (Previously Presented) The method of claim 7 wherein the ring of resist protects device formed in the further region of said substrate from shining spots present in said periphery of said substrate.

35. (New) A method of forming at least one device in a substrate, said method comprising:

- depositing a pad oxide layer atop said substrate;
- depositing a pad nitride layer atop said pad oxide layer;
- depositing a hard mask layer atop said nitride layer;
- depositing a layer of resist atop said hard mask layer;
- patterning said layer of resist to form a ring of resist, said ring of resist separating a periphery of said substrate from a further region of said substrate;
- depositing a further layer of resist atop said hard mask layer and atop said ring of resist;
- patterning said further layer of resist to form at least one patterned region within said further region of said substrate, said ring of resist being of sufficient thickness that a region of said further layer of resist that is atop said ring of resist is not patterned;
- etching said hard mask layer using said patterned further layer of resist and said ring of resist as an etch mask;
- removing the further layer of resist after etching said hard mask layer; and
- after removing the further layer of resist, etching at least one trench region in said substrate using said hard mask layer and said ring of resist as an etch mask, said ring of resist being of sufficient thickness that a region of said hard mask layer that is beneath said ring of resist remains after said trench region is etched.